

<b>INFORMATION DISCLOSURE STATEMENT PTO-1449</b>	Atty. Docket No. <b>011227</b>	Serial No. New Appln.
	Applicant(s): <b>Koki MUKAI</b>	
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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					
_____	AE					

### FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
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### OTHER DOCUMENTS

	AI	T. FUKUI, et al., GaAs Tetrahedral Quantum Dot Structure Fabricated using Selective Area Metalorganic Chemical Vapor Deposition, App. Phys. Letter 58(18), May 6, 1991, pp. 2018-2020
	AJ	S.K. Mathis, et al., Strain Relaxation of InGaAs by Lateral Oxidation of AIAs, J. Vac. Sci. Technol. B18(4), June/August 2000, pp. 2066-2071
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